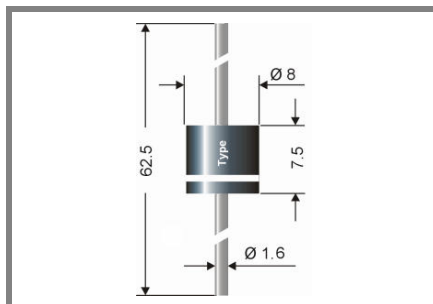


# P 800 ATL ... P 800 STL



## Axial lead diode

## Standard silicon rectifier diodes

### P 800 ATL ... P 800 STL

**Forward Current: 8 A**

**Reverse Voltage: 50 to 1200 V**

Preliminary Data

### Features

- Max. solder temperature: 260 °C
- Plastic material has UL classification 94V-0

### Mechanical Data

- Plastic case: 8 x 7,5 [mm]
- Weight approx.: 1,9 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 500 pieces per ammo or 1000 pieces per reel

1) Valid, if leads are kept at  $T_A$  at a distance of 10 mm from case

2)  $I_F = 5 A$ ,  $T_j = 25 °C$

3)  $T_A = 25 °C$

4) Thermal resistance from junction to lead/terminal at a distance 0 mm from case

5) Max. junction temperature  $T_j \leq 200 °C$  in bypass mode / DC forward mode

Type	Repetitive peak reverse voltage $V_{RRM}$ V	Surge peak reverse voltage $V_{RSM}$ V	Max. reverse recovery time $I_F = - A$ $I_R = - A$ $I_{RR} = - A$ $t_{rr}$ ns	Max. forward voltage $V_F^{(2)}$
P800A TL	50	50	-	1,0
P800B TL	100	100	-	1,0
P800D TL	200	200	-	1,0
P800G TL	400	400	-	1,0
P800J TL	600	600	-	1,0
P800K TL	800	800	-	1,0
P800M TL	1000	1000	-	1,0
P800S TL	1200	1200	-	1,0

### Absolute Maximum Ratings

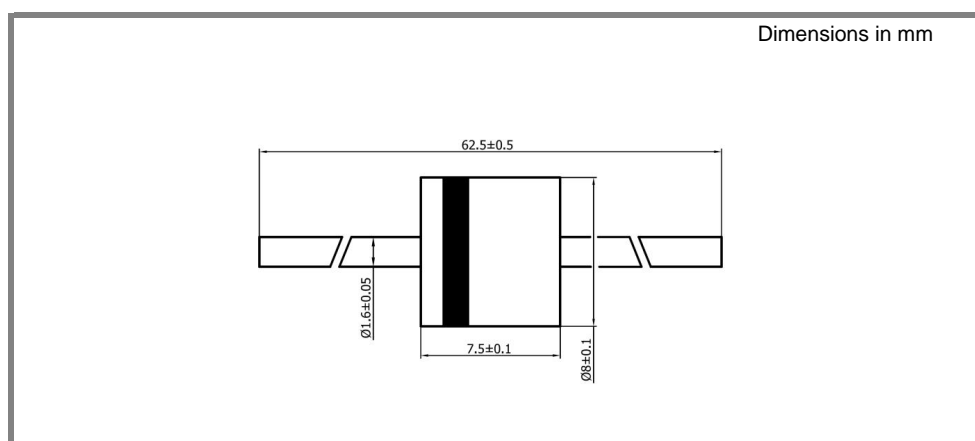
$T_A = 25 °C$ , unless otherwise specified

Symbol	Conditions	Values	Units
$I_{FAV}$	Max. averaged fwd. current, R-load, $T_A = 50 °C$ <sup>1)</sup>	8	A
$I_{FRM}$	Repetitive peak forward current $f > 15 Hz$ <sup>1)</sup>	65	A
$I_{FSM}$	Peak forward surge current 50 Hz half sinus-wave <sup>3)</sup>	400	A
$i^2t$	Rating for fusing, $t < 10 ms$ <sup>3)</sup>	800	A <sup>2</sup> s
$R_{thA}$	Max. thermal resistance junction to ambient <sup>1)</sup>		K/W
$R_{thL}$	Max. thermal resistance junction to terminals <sup>4)</sup>	1,8	K/W
$T_j$	Operating junction temperature	- 50 ... + 175 ( $T_j \leq 200 °C$ in bypass mode <sup>5)</sup> )	°C
$T_s$	Storage temperature	- 50 ... + 175	°C

### Characteristics

$T_A = 25 °C$ , unless otherwise specified

Symbol	Conditions	Values	Units
$I_R$	Maximum leakage current, $T_j = 25 °C$ ; $V_R = V_{RRM}$	<25	µA
	$T_j = °C$ ; $V_R = V_{RRM}$		
$C_j$	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
$Q_{rr}$	Reverse recovery charge ( $U_R = V$ ; $I_F = A$ ; $di_F/dt = A/ms$ )	-	µC
$E_{RSM}$	Non repetitive peak reverse avalanche energy ( $I_R = mA$ ; $T_j = °C$ ; inductive load switched off)	-	mJ



case: 8 x 7,5 [mm]

